

isc Silicon NPN Power Transistor

2SD155

DESCRIPTION

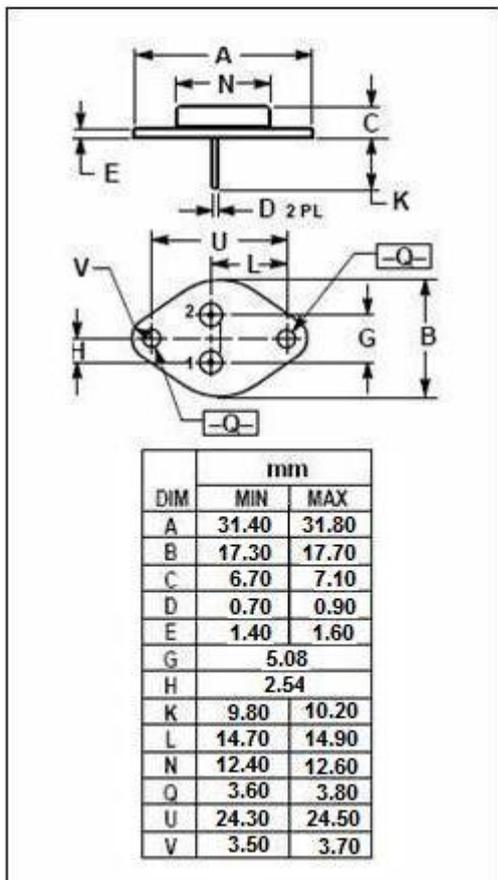
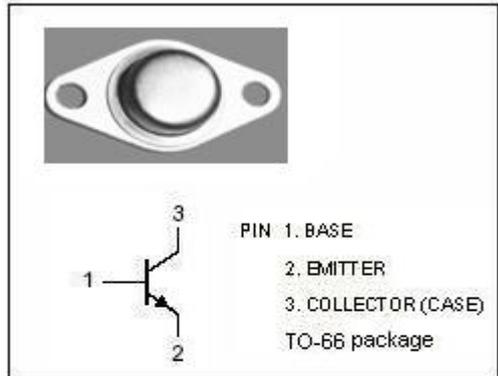
- Low Collector Saturation Voltage
: $V_{CE(sat)} = 1.0V(\text{Max}) @ I_C = 2A$
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 80V(\text{Min})$
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	3.0	A
I_{CM}	Collector Current-Peak	5.0	A
I_B	Base Current	1.0	A
P_C	Collector Power Dissipation@ $T_C = 25^\circ\text{C}$	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SD155****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}; I_B=0$	80			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=100\ \mu\text{A}; I_E=0$	80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=100\ \mu\text{A}; I_C=0$	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.2\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.2\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=80\text{V}; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	μA
h_{FE-1}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=2\text{V}$	60		320	
h_{FE-2}	DC Current Gain	$I_C=2\text{A}; V_{CE}=2\text{V}$	20			
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f=1\text{MHz}$		40		pF